

# SI-3000ZD Series Surface-Mount, Low Dropout Voltage

## ■Features

- Compact surface-mount package (TO263-5)
- Output current: 3.0A
- Low dropout voltage:  $V_{DIF} \leq 0.6V$  (at  $I_o = 3.0A$ )
- Low circuit current at output OFF:  $I_q (\text{OFF}) \leq 1\mu A$
- Built-in overcurrent and thermal protection circuits

## ■Applications

- Secondary stabilized power supply (local power supply)

## ■Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	( $T_a=25^\circ C$ )
DC Input Voltage	$V_{IN}^{*1}$	10	V	
Output Control Terminal Voltage	$V_c$	6	V	
DC Output Current	$I_o^{*1}$	3.0	A	
Power Dissipation	$P_d^{*3}$	3	W	
Junction Temperature	$T_j$	-30 to +125	$^\circ C$	
Operating Ambient Temperature	$T_{op}$	-30 to +85	$^\circ C$	
Storage Temperature	$T_{stg}$	-40 to +125	$^\circ C$	
Thermal Resistance (Junction to Ambient Air)	$\theta_{j-a}$	33.3	$^\circ C/W$	
Thermal Resistance (Junction to Case)	$\theta_{j-c}$	3	$^\circ C/W$	

## ■Recommended Operating Conditions

Parameter	Symbol	Ratings	Unit	Remarks
Input Voltage	$V_{IN}$	$^{*2} 2$ to $6^{*1}$	V	
Output Current	$I_o$	0 to 3	A	
Operating Ambient Temperature	$T_{op}$ (a)	-20 to +85	$^\circ C$	
Operating Junction Temperature	$T_{op}$ (j)	-20 to +100	$^\circ C$	
Output Voltage Variable Range	$V_{ADJ}$	1.2 to 5	V	Only for SI-3011ZD. Refer to the block diagram.

\*1:  $V_{IN}$  (max) and  $I_o$  (max) are restricted by the relation  $P_o = (V_{IN} - V_o) \times I_o$ .

\*2: Set the input voltage to 2.4V or higher when setting the output voltage to 2.0V or lower (SI-3011ZD).

\*3: When mounted on glass-epoxy board of 40 × 40mm (copper laminate area 100%).

## ■Electrical Characteristics

( $T_a=25^\circ C$ ,  $V_c=2V$ , unless otherwise specified)

Parameter	Symbol	SI-3011ZD (Variable type)			SI-3033ZD			Unit
		min.	typ.	max.	min.	typ.	max.	
Output Voltage (Reference Voltage $V_{ADJ}$ for SI-3011ZD)	$V_o (V_{ADJ})$	1.078	1.100	1.122	3.234	3.300	3.366	V
	Conditions	$V_{IN}=V_o+1V$ , $I_o=10mA$			$V_{IN}=5V$ , $I_o=10mA$			
Line Regulation	$\Delta V_{OLINE}$			10			10	mV
	Conditions	$V_{IN}=3.3$ to 5V, $I_o=10mA$ ( $V_o=2.5V$ )			$V_{IN}=4.5$ to 5.5V, $I_o=10mA$			
Load Regulation	$\Delta V_{LOAD}$			40			40	mV
	Conditions	$V_{IN}=3.3V$ , $I_o=0$ to 3A ( $V_o=2.5V$ )			$V_{IN}=5V$ , $I_o=0$ to 3A			
Dropout Voltage	$V_{DIF}$			0.6			0.6	V
	Conditions	$I_o=3A$ ( $V_o=2.5V$ )			$I_o=3A$			
Quiescent Circuit Current	$I_q$		1	1.5			1	mA
	Conditions	$V_{IN}=V_o+1V$ , $I_o=0A$ , $V_c=2V$			$V_{IN}=5V$ , $I_o=0A$ , $V_c=2V$			
Circuit Current at Output OFF	$I_q$ (OFF)			1			1	$\mu A$
	Conditions	$V_{IN}=V_o+1V$ , $V_c=0V$			$V_{IN}=5V$ , $V_c=0V$			
Temperature Coefficient of Output Voltage	$\Delta V_o/\Delta T_a$		$\pm 0.3$				$\pm 0.3$	$mV/^\circ C$
	Conditions	$T_j=0$ to 100 $^\circ C$			$T_j=0$ to 100 $^\circ C$			
Ripple Rejection	$R_{REJ}$		60				60	dB
	Conditions	$V_{IN}=V_o+1V$ , $f=100$ to 120Hz, $I_o=0.1A$			$V_{IN}=5V$ , $f=100$ to 120Hz, $I_o=0.1A$			
$I_{S1}$ <sup>*4</sup>		3.2			3.2			A
	Conditions	$V_{IN}=V_o+1V$			$V_{IN}=5V$			
$V_c$ Terminal	Control Voltage (Output ON) <sup>*3</sup>	$V_c$ , IH	2		2			V
	Control Voltage (Output OFF) <sup>*3</sup>	$V_c$ , IL		0.8			0.8	
	Control Current(Output ON)	$I_c$ , IH		100			100	$\mu A$
	Control Current(Output OFF)	$I_c$ , IL	-5	0	-5	0		
	Conditions	$V_c=2.7V$			$V_c=2.7V$			
	Conditions	$V_c=0V$			$V_c=0V$			$\mu A$

\*1: Set the input voltage to 2.4V or higher when setting the output voltage to 2.0V or lower.

\*2:  $I_{S1}$  is specified at the -5% drop point of output voltage  $V_o$  under the condition of Output Voltage parameter.

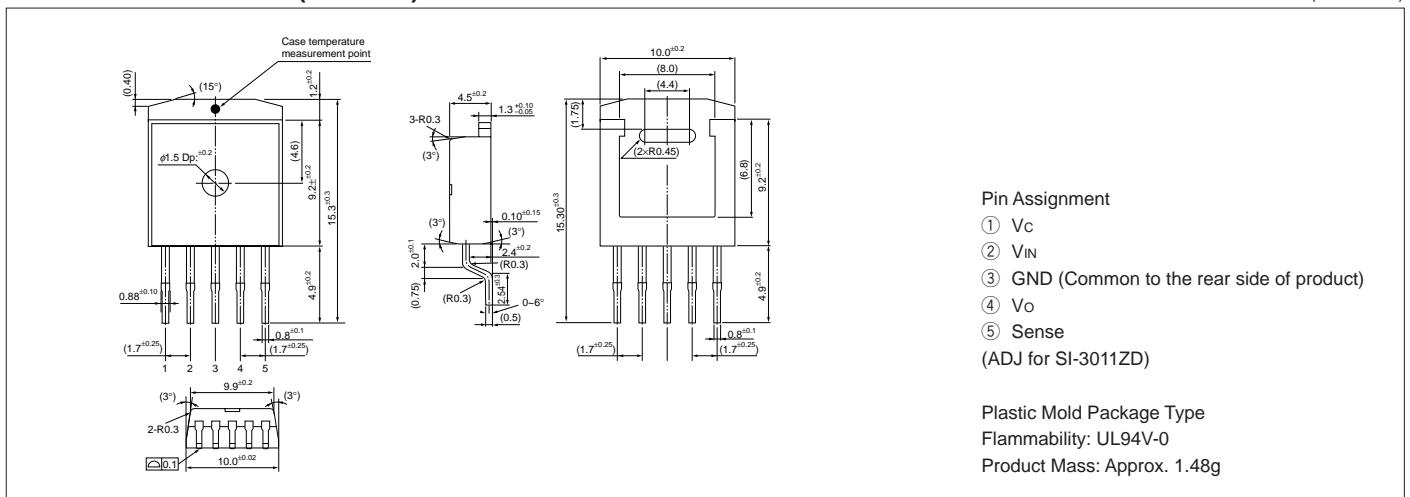
\*3: Output is OFF when the output control terminal ( $V_c$  terminal) is open. Each input level is equivalent to LS-TTL level. Therefore, the device can be driven directly by LS-TTLs.

\*4: These products cannot be used for the following applications because the built-in foldback-type overcurrent protection may cause errors during start-up stage.

(1) Constant current load (2) Positive and negative power supply (3) Series-connected power supply (4)  $V_o$  adjustment by raising ground voltage

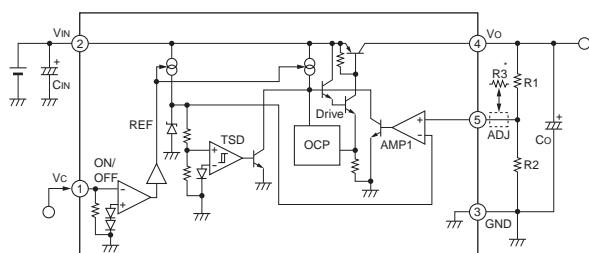
## ■External Dimensions (TO263-5)

(Unit : mm)



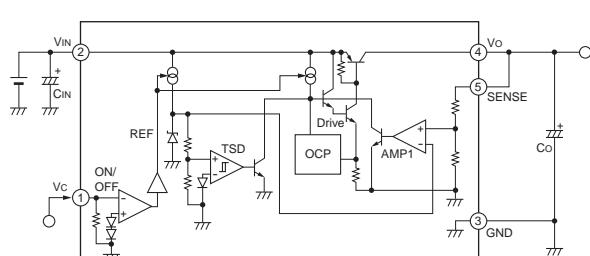
## ■Block Diagram

SI-3011ZD

C<sub>IN</sub>: Input capacitor (Approx. 10μF)C<sub>O</sub>: Output capacitor (47μF or larger)

The output voltage may oscillate if a low ESR type capacitor (such as a ceramic capacitor) is used for the output capacitor in the SI-3000ZD Series.

SI-3033ZD

R<sub>1</sub>, R<sub>2</sub>: Output voltage setting resistors

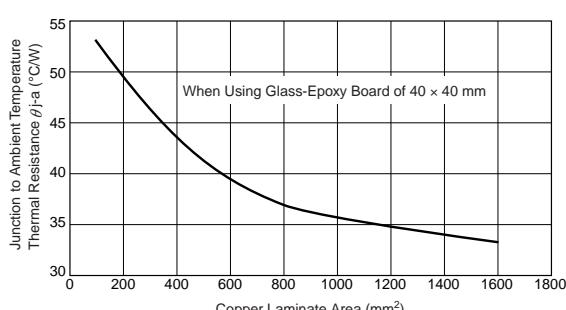
The output voltage can be set by connecting R<sub>1</sub> and R<sub>2</sub> as shown at left.  
The recommended value for R<sub>2</sub> is 10kΩ or 11kΩ.

$$R_1 = (V_O - V_{ADJ}) / (V_{ADJ}/R_2)$$

\*: Insert R<sub>3</sub> in case of setting Vo to Vo ≤ 1.8V. The recommended value for R<sub>3</sub> is 10kΩ.

## ■Reference Data

Copper Laminate Area (on Glass-Epoxy Board) vs.  
Thermal Resistance (from Junction to Ambient Temperature) (Typical Value)



- A higher heat radiation effect can be achieved by enlarging the copper laminate area connected to the inner frame to which a monolithic IC is mounted.
- Obtaining the junction temperature  
Measure GND terminal temperature T<sub>c</sub> with a thermocouple, etc. Then substitute this value in the following formula to obtain the junction temperature.

$$T_j = P_D \times \theta_{j-a} + T_c \quad P_D = (V_{IN} - V_o) \times I_{OUT}$$